

CCE in irradiated silicon detectors with a consideration of avalanche effect

Tuesday 17 November 2009 10:15 (20 minutes)

The results of modeling of CCE vs. fluence and CCE vs. voltage dependences in a wide range of fluences and bias voltage are presented. The shape of the curves is discussed in the frame of PTI model for avalanche multiplication in p-n junctions on deep level rich semiconductors.

Author: Dr EREMIN, Vladimir (Ioffe Physical-Technical Institute RAS)

Co-authors: Prof. ZABRODSKII, Andrei (Ioffe Physical-Technical Institute RAS); Dr VERBITSKAYA, Elena (Ioffe Physical-Technical Institute RAS); Dr HÄRKÖNEN, Jaakko (Helsinki Institute of Physics, CERN/PH.); Dr LI, Zheng (Brookhaven National Laboratory)

Presenter: Dr EREMIN, Vladimir (Ioffe Physical-Technical Institute RAS)

Session Classification: Pad Detector Characterization & Studies on Charge Multiplication